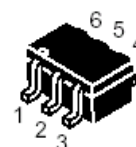


# Silicon PNP Epitaxial Planer Transistor

**L4401DW1T1**

**SC88**

## MAXIMUM RATINGS

Parameter	Symbol	Ratings	Unit
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Collector-Base Voltage	$V_{CBO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector current-continuoun	$I_C$	-150	mAdc

## THERMAL CHARATEERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A=25^\circ\text{C}$	$P_D$	380	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^\circ\text{C/W}$
Junction and Storage Temperature	$T_j, T_{stg}$	-55 to +150	$^\circ\text{C}$

## DEVICE MARKING

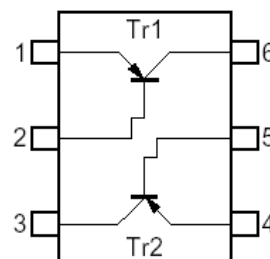
L4401DW1T1=5K

## ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C=-1\text{mA}$ )	$V_{(BR)CEO}$	-50	-	-	V
Emitter-Base Breakdown Voltage ( $I_E=-50\ \mu\text{A}$ )	$V_{(BR)EBO}$	-6	-	-	V
Collector-Base Breakdown Voltage ( $I_C=-50\ \mu\text{A}$ )	$V_{(BR)CBO}$	-60	-	-	V



Collector Cutoff Current ( $V_{CB}=-60V$ )	ICBO	-	-	-0.1	$\mu A$
Emitter Cutoff Current ( $V_{BE}=-6V$ )	IEBO			-0.1	$\mu A$

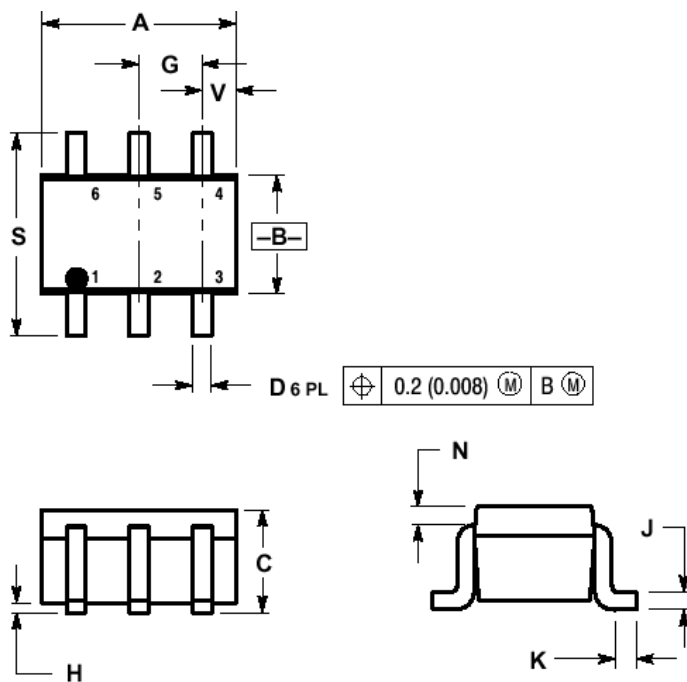
**ON CHARACTERISTICS**

DC Current Gain ( $I_C=-1mA, V_{CE}=-6.0V$ )	Hfe	120	-	560	
Collector-Emitter Saturation Voltage ( $I_C=-50mA, I_B=-5mA$ )	VCE(SAT)	-	-	-0.5	V

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $V_{CE} = -12.0V; I_E = 2.0 mA, f=300MHz$ )	Ft	-	140	-	MHz
Output Capacitance( $V_{CB}=-12V, f=1.0MHz$ )	Cobo	-	4	5	Pf

**PACKAGE DIMENSIONS  
SC-88**



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026BSC		0.65BSC	
H	—	0.004	—	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40